

**Proceedings of the  
20<sup>th</sup> INTERNATIONAL SYMPOSIUM  
on  
POWER SEMICONDUCTOR DEVICES &  
ICS**

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# TABLE OF CONTENTS

Welcome from the Chairman .....	iii
Conference Committees .....	iv
Call for Papers ISPSD 2009 .....	vi
Best Paper ISPSD 2008 .....	vii
G. Charitat Award .....	x

## Monday - May 19, 2008

**8:45 am – 11:00 am**

### **SESSION 1 (P1) – Plenary**

**Chairs:** T.P. Chow, *Rensselaer Polytechnic Institute*  
J. Millan, *CNM*

**8:45 am – 9:30 am**

<b>P1-1 Environmental Trends and Opportunities for Computer Power Delivery .....</b>	<b>1</b>
Edward Stanford, <i>Intel</i>	

**9:30 am – 10:15 am**

<b>P1-2 A New AC Current Switch Called MERS with Low On-State Voltage IGBTs (1.54 V) for Renewable Energy and Power Saving Applications .....</b>	<b>4</b>
Ryuichi Shimada, Jan A. Wiik, and Takanori Isobe, <i>Tokyo Institute of Technology</i> ; Taku Takaku and Noriyuki Iwamuro, <i>Fuji Electric Device Technology Co., Ltd.</i> ; Yoshiyuki Uchida, <i>Curamik Electronics KK</i> ; Marta Molinas and Tore M. Undeland, <i>Norwegian University of Science and Technology</i>	

**10:15 am – 11:00 am**

<b>P1-3 From Packaging to "Un"-Packaging – Trends in Power Semiconductor Modules .....</b>	<b>12</b>
Thomas Stockmeier, <i>SEMIKRON Elektronik GmbH &amp; Co KG</i>	

**1:30 pm – 3:10 pm**

### **SESSION 2 (LV1) – Trench MOSFETs and Lateral IGBT**

**Chairs:** Gary Dolny, *Fairchild Semiconductor*  
Jan Sonsky, *NXP*

**1:30 pm – 1:55 pm**

<b>LVI-1 A 30V EDMOS with Orthogonal Gate Structure Based on a 0.18<math>\mu</math>m CMOS Technology .....</b>	<b>20</b>
Hao Wang, H.P. Edward Xu, and Wai Tung Ng, <i>University of Toronto</i> ; Kenji Fukumoto, Ken Abe, Akira Ishikawa, Hisaya Imai, Kimio Sakai, and Kaoru Takasuka, <i>Asahi Kasei EMD</i>	

**1:55 pm – 2:20 pm**

<b>LVI-2 60V Lateral Trench MOSFET in 0.35 <math>\mu</math>m Technology .....</b>	<b>24</b>
Don Disney, Wilson Chan, Roy Lam, Robert Blattner, Steve Ma, Wesley Seng, Jun-Wei Chen, Michael Cornell, and Richard Williams, <i>Advanced Analogic Technologies, Inc.</i>	

**2:20 pm – 2:45 pm**

<b>LVI-3 A Fully Realized 'Field Balanced' TrenchMOS Technology .....</b>	<b>28</b>
Steven T. Peake, Phil Rutter, Steve Hodgskiss, Mark Gajda, and Neil Irwin, <i>NXP Semiconductors</i>	

**2:45 pm – 3:10 pm**

**LVI-4 Retrograded Channel SOI LIGBTs with Enhanced Safe Operating Area** ..... 32  
David Hongfei Lu, Tomonori Mizushima, Akio Kitamura, Noriyuki Iwamuro, and Naoto Fujishima, *Fuji Electric Device Technology Co., Ltd.*

**3:30 pm – 5:10 pm**

**SESSION 3 (HV1) – Novel High Voltage Devices**

**Chairs:** M.K. Han, *Seoul National University*  
Reinhard Herzer, *Semikron International*

**3:30 pm – 3:55 pm**

**HV1-1 An IGCT Chip Set for 7.2 kV (RMS) VSI Application** ..... 36  
Iulian Nistor, Maxi Scheinert, Tobias Wikström, and Mathias Lüscher, *ABB Switzerland Ltd., Semiconductors*

**3:55 pm – 4:20 pm**

**HV1-2 Experimental Study of a 6.5kV MOS Controllable Freewheeling Diode** ..... 40  
J.G. Bauer, T. Duetemeyer, F. Hille, and O. Humbel, *Infineon Technologies AG*

**4:20 pm – 4:45 pm**

**HV1-3 A Trial Simulation on the Cosmic Ray Induced Failure of the Long  $n^-$  Length pin Diodes** ..... 44  
Ikunori Takata, *Mitsubishi Electric Corp.*

**4:45 pm – 5:10 pm**

**HV1-4 Experimental Demonstration of 3.3kV Planar CIGBT in NPT Technology** ..... 48  
M. Sweet, N. Luther-King, S.T. Kong, and E.M. Sankara Narayanan, *University of Sheffield*; J. Bruce and Shona Ray, *Semefab Scotland Ltd.*

## **Tuesday - May 20, 2008**

**8:30 am – 10:10 am**

**SESSION 4 (IP1) – Integration Technologies**

**Chairs:** Peter Moens, *AMI Semiconductor*  
Sameer Pendharkar, *Texas Instruments*

**8:30 am – 8:55 am**

**IP1-1 High-Voltage Technology Based on Thin Layer SOI for Driving Plasma Display Panels** ..... 52  
Ming Qiao, Bo Zhang, Zhiqiang Xiao, Jian Fang, and Zhaoji Li, *University of Electronic Science and Technology of China*

**8:55 am – 9:20 am**

**IP1-2 HVCMOS8A: 22V-42V Rated MOS Integration in a 0.18 $\mu$ m Technology Platform for High Voltage Applications** ..... 56  
Stephane Bach, Laura Atzeni, Antonio Molfese, Alessandro Dundulachi, Elisabetta Castellana, Giuseppe Croce, Claudio Contiero, *STMicroelectronics*

**9:20 am – 9:45 am**

**IP1-3 55V Integrated Power and Non-Volatile Technology for Solid State Lighting Applications** ..... 60  
T. Letavic, R. Cook, S. Sharma, R. Brock, C. Mandhare, H. Effing, D. Dormans, B. Daniel, P. Deurenberg, C. Rooijackers, and R. de Nie, *NXP Semiconductors*

9:45 am – 10:10 am

**IP1-4 BD180 – A New 0.18  $\mu\text{m}$  BCD (Bipolar-CMOS-DMOS) Technology from 7V to 60V** ..... 64  
I-Yong Park, Yong-Keon Choi, Kwang-Young Ko, Chul-Jin Yoon, Bon-Keun Jun, Mi-Young Kim, Hyon-Chol Lim,  
Nam-Joo Kim, and Kwang-Dong Yoo, *Dongbu HiTek*

10:30 am – 12:10 pm

**SESSION 5 (HV2) – IGBT and Diode**

**Chairs:** Stefan Linder, *ABB*

Seki Yasukazu, *Fuji Electric*

10:30 am – 10:55 am

**HV2-1 A High Current 3300V Module Employing Reverse Conducting IGBTs  
Setting a New Benchmark in Output Power Capability** ..... 68  
M. Rahimo, U. Schlapbach, A. Kopta, J. Vobecky, D. Schneider, and A. Baschnagel, *ABB Switzerland Ltd.,  
Semiconductors*

10:55 am – 11:20 am

**HV2-2 CSTBT™ (III) as the Next Generation IGBT** ..... 72  
Tetsuo Takahashi, Yoshifumi Tomomatsu, and Katsumi Sato, *Mitsubishi Electric Corporation*

11:20 am – 11:45 am

**HV2-3 Exploring the Silicon Design Limits of Thin Wafer IGBT Technology:  
The Controlled Punch Through (CPT) IGBT** ..... 76  
J. Vobecký, M. Rahimo, A. Kopta, and S. Linder, *ABB Switzerland Ltd., Semiconductors*

11:45 am – 12:10 pm

**HV2-4 Development of the 1200V FZ-Diode with Soft Recovery Characteristics  
by the New Local Lifetime Control Technique** ..... 80  
Y. Onozawa, K. Takahashi, H. Nakano, M. Nemoto, M. Otsuki, O. Ikawa, and T. Miyasaka, *Fuji Electric Device  
Technology Co., Ltd.*

1:00 pm – 4:00 pm

**SESSION 6 (LV-P) – Low Voltage Posters**

**LV-P-1  $\mu$ -Raman Validated Stress-Enhanced Mobility in XtremeMOS Transistors** ..... 84  
P. Moens, J. Roig, J. Meersman, J. Baele, B. Desoete, and M. Tack, *AMI Semiconductor*; I. De Wolf, *IMEC*

**LV-P-2 Scalable Spice Modeling of Integrated Power LDMOS Device  
Using a Cell-Based Building Block Approach** ..... 88  
Yong Qiang Li, Tracey Krakowski, Pascale Francis, and Linda Smith, *National Semiconductor*

**LV-P-3 A Novel Sub-20V Power MOSFET with Improved On-Resistance and Threshold Variation** ..... 91  
Jacky C.W. Ng and Johnny K.O. Sin, *Hong Kong University of Science and Technology*; Lingpeng Guan, *Alpha &  
Omega Semiconductor, Inc.*

**LV-P-4 High Performance Low-Voltage Power MOSFETs with Hybrid Waffle  
Layout Structure in a 0.25 $\mu\text{m}$  Standard CMOS Process** ..... 95  
Abraham Yoo, Marian Chang, Olivier Trescases, and Wai Tung Ng, *University of Toronto*

<b>LV-P-5 Optimization of Body Diode Reverse Recovery Characteristics of Lateral Power MOSFETs for Synchronous Rectifier DC-DC Converters</b> .....	99
<i>Y. Xiong, H. Jia, W. Deschain, S. Sun, and X. Cheng, University of Central Florida; G. Dashney and D. Okada, Great Wall Semiconductor; Z.J. Shen, University of Central Florida</i>	
<b>LV-P-6 Implementation of 85V High Side LDMOS with n-layer in a 0.35um BCD Process</b> .....	103
<i>Choul-Joo Ko, Sang-Yong Lee, Il-Yong Park, Cho-Eung Park, Bon-Keun Jun, Yong-Jun Lee, Chan-Hee Kang, Jae-O Lee, Nam-Joo Kim, and Kwang-Dong Yoo, Dongbu HiTek</i>	
<b>LV-P-7 High Side n-channel and Bidirectional Trench Lateral Power MOSFETs on One Chip for DCDC Converter ICs</b> .....	107
<i>Mutsumi Sawada, Masaharu Yamaji, Shinichiro Matsunaga, Masanobu Iwaya, Hidenori Takahashi, Tsuyoshi Yoshiki, Akihiro Jonishi, Akio Kitamura, and Naoto Fujishima, Fuji Electric Device Technology Co., Ltd.</i>	
<b>LV-P-8 SJ-FINFET: A New Low Voltage Lateral Superjunction MOSFET</b> .....	111
<i>Y. Onishi, Fuji Electric Device Technology Co., Ltd.; H. Wang, H.P.E. Xu, and W.T. Ng, University of Toronto; R. Wu and J.K.O. Sin, Hong Kong University of Science and Technology</i>	
<b>LV-P-9 New Power MOSFET Employing Segmented Trench Body Contact for Improving the Avalanche Energy</b> .....	115
<i>In-Hwan Ji, Kyu-Heon Cho, and Min-Koo Han, Seoul National University; Seung-Chul Lee, Soo-Seong Kim, Kwang-Hoon Oh, and Chong-Man Yun, Fairchild Semiconductor</i>	
<b>LV-P-10 An 80V Class Silicon Lateral Trench Power MOSFET for High Frequency Switching Applications</b> .....	119
<i>K.R. Varadarajan, and T.P. Chow, Rensselaer Polytechnic Institute; R. Liu, F. Gonzalez, and B. Choy, Supertex</i>	
<b>LV-P-11 3D-Resurf: The Integration of a p-Channel LDMOS in a Standard CMOS Process</b> .....	123
<i>V. Vescoli, J.M. Park, S. Carniello, and R. Minixhofer, austriamicrosystems AG</i>	
<b>LV-P-12 Evaluation of Trench-Gate Bipolar-Mode JFETs used as High-Side Transistors in Low-Voltage Buck Converters</b> .....	127
<i>Yu Wu, Bo Tian, Huai Huang, and Dongqing Hu, Beijing University of Technology; Johnny K.O. Sin, Hong Kong University of Science and Technology; Baowei Kang, Beijing University of Technology</i>	
<b>LV-P-13 A Gate-Controllable High-Voltage SCR Device with High Performance in ESD Protection and Latch-Up Immunity</b> .....	131
<i>Tuo-Hsin Chien and Klaus Y.-J. Hsu, National Tsing Hua University</i>	
<b>SESSION 6 (HV-P) – High Voltage Posters</b>	
<b>HV-P-1 Determination of Manufacturing Resurf Process Window for a Robust 700V Double Resurf LDMOS Transistor</b> .....	133
<i>Zia Hossain, ON Semiconductor</i>	
<b>HV-P-2 Investigation of Dynamic Avalanche in the Termination Region for FWDs with High Reverse Recovery Capability</b> .....	137
<i>Satoru Kameyama, Toyota Motor Corporation; Takahide Sugiyama, Toyota Central R&amp;D Labs Inc.; Ryuzo Tagami and Katsuhiko Nishiwaki, Toyota Motor Corporation</i>	
<b>HV-P-3 700V Lateral DMOS with New Source Fingertip Design</b> .....	141
<i>S.H. Lee, C.K. Jeon, J.W. Moon, and Y.C. Choi, Fairchild Korea Semiconductor</i>	

<b>HV-P-4 The Next Generation of HV-IGBTs with Low Loss and High SOA Capability</b> .....	145
<i>Katsumi Nakamura, Kenji Hatori, and Yoshiaki Hisamoto, Mitsubishi Electric Corporation; Shunsuke Sakamoto, Fukuryo Semicon Engineering Corporation; Tatsuo Harada, and Kazunari Hatade, Mitsubishi Electric Corporation</i>	
<b>HV-P-5 A New Optimized 200V Low on-Resistance Power FLYMOSFET</b> .....	149
<i>Y. Weber, CNRS;LAAS, Université de Toulouse;UPS;LAAS, Freescale Semiconducteurs France SAS; F. Morancho, CNRS;LAAS, Université de Toulouse;UPS;LAAS; J.-M. Reynes, Freescale Semiconducteurs France SAS; E. Stefanov, Freescale Semiconducteurs France SAS</i>	
<b>HV-P-6 Analysis of a p+p-n-n+ Diode Structure</b> .....	153
<i>Min Chen and Josef Lutz, Chemnitz University of Technology; Hans-Peter Felsl and Hans-Joachim Schulze, Infineon Technologies AG</i>	
<b>HV-P-7 JFET Depletion in SuperJunction Devices</b> .....	157
<i>Don Disney, Advanced Analogic Technologies, Inc.; Gary Dolny, Fairchild Semiconductor</i>	
<b>HV-P-8 The Optimal Profile Design for SJ-MOSFET Fabricated by Double-Ion-Implantation and Multi-Epitaxial Method</b> .....	161
<i>Syotaro Ono, Wataru Saito, Masaru Izumisawa, Yasuto Sumi, Shoichiro Kurushima, Masataka Tsuji, Ken'ichi Tokano, and Masakazu Yamaguchi, Semiconductor Company, Toshiba Corporation</i>	
<b>HV-P-9 Super Junction MOSFETs Above 600V with Parallel Gate Structure Fabricated by Deep Trench Etching and Epitaxial Growth</b> .....	165
<i>A. Sugi, M. Takei, K. Takahashi, A. Yajima, H. Tomizawa, and H. Nakazawa, Fuji Electric Device Technology Co., Ltd.</i>	
<b>HV-P-10 Anode Design Variation in 1200-V Trench Field-Stop Reverse-Conducting IGBTs</b> .....	169
<i>S. Voss, F.J. Niedernostheide, and H.J. Schulze, Infineon Technologies AG</i>	
<b>HV-P-11 The CIBH Diode – Great Improvement for Ruggedness and Softness of High Voltage Diodes</b> .....	173
<i>H.P. Felsl, M. Pfaffenlehner, H. Schulze, J. Biermann, Th. Gutt, and H.-J. Schulze, Infineon Technologies AG; M. Chen, and J. Lutz, Chemnitz University of Technology</i>	
<b>HV-P-12 A Study of the Influence of Technology on the Negative Gate Capacitance in 1.2kV IGBTs</b> ....	177
<i>S.T. Kong, L. Ngwendson, M. Sweet, and E.M. Sankara Narayanan, University of Sheffield</i>	
<b>HV-P-13 Thermal and Structural Simulation Techniques for Estimating Fatigue Life of an IGBT Module</b> .....	181
<i>Koji Sasaki and Naoko Iwasa, Mechanical Engineering Research Laboratory, Hitachi, Ltd.; Toshiki Kurosu, Katsuaki Saito, Yoshihiko Koike, Yukio Kamita, and Yasushi Toyoda, Power &amp; Industrial Systems Division, Hitachi, Ltd.</i>	
<b>HV-P-14 Critical IGBT Design Regarding EMI and Switching Losses</b> .....	185
<i>Masanori Tsukuda, Ichiro Omura, Yoko Sakiyama, Masakazu Yamaguchi, Ken'ichi Matsushita, and Tsuneo Ogura, Semiconductor Company, Toshiba Corporation</i>	
<b>HV-P-15 A Study on the Reliability of the Chip Surface Solder Joint</b> .....	189
<i>Yoshinari Ikeda, Yuji Iizuka, Tatsuhiko Asai, Tomoaki Goto, and Yoshikazu Takahashi, Fuji Electric Device Technology Co., Ltd.</i>	
<b>HV-P-16 New Oscillation Circuit Discovered in Switching-Mode Power Supplies</b> .....	193
<i>T. Fujihira, T. Yamada, Y. Minoya, T. Kobayashi, Y. Niimura, T. Kuboyama, R. Araki, and H. Ota, Fuji Electric Device Technology Co., Ltd.</i>	

## SESSION 6 (IP-P) – Interated Power Posters

<b>IP-P-1 Chipset for Flexible and Scalable High-Performance Gate Drivers for 1200V- 6500V IGBTs .....</b>	<b>197</b>
<i>Jan Thalheim, CT-Concept Technologie AG</i>	
<b>IP-P-2 Self-Triggered SCR in Output Driver for Enhanced ESD Robustness .....</b>	<b>201</b>
<i>TaegHyun Kang, JunHyeong Ryu, and MoonHo Kim, Fairchild Semiconductor; EuiYong Chung, Yonsei University; Donna Robinson-Hahn, Fairchild Semiconductor</i>	
<b>IP-P-3 Time Dependent Isolation Capability of High Voltage Deep Trench Isolation .....</b>	<b>205</b>
<i>Ralf Lerner, Uwe Eckoldt, and Klaus Schottmann, X-FAB Semiconductor Foundries AG; Steffen Heinz, Klaus Erler, Andre Lange, and Gunter Ebest, Chemnitz University of Technology</i>	
<b>IP-P-4 Measurement and Simulation of Self-Heating in DMOS Transistors up to Very High Temperatures .....</b>	<b>209</b>
<i>Martin Pfost, Joachim Joos, and Matthias Stecher, Infineon Technologies AG</i>	
<b>IP-P-5 Integrated Photoreceiver for an Isolated Control Signal Transfert in Favour of Power Transistors .....</b>	<b>213</b>
<i>Nicolas Rouger and Jean-Christophe Crébier, University of Grenoble</i>	
<b>IP-P-6 Sense Device Structure in Hybrid IGBT with Constant Current Sense Ratio for Entire Collector Current Range .....</b>	<b>217</b>
<i>H. Yamagiwa, T. Saji, S. Kaneko, S. Takahashi, T. Uno, and K. Sawada, Matsushita Electric Industrial Co., Ltd.</i>	
<b>IP-P-7 ESD Protection of NDMOS in 0.18<math>\mu</math>m High-Voltage CMOS Technology for Automotive Applications .....</b>	<b>221</b>
<i>L. Steinbeck and U. Pröhl, X-FAB Dresden GmbH &amp; Co. KG; M. Frank and A. Konrad, X-FAB Semiconductor Foundries AG; C. Ellmers and T. Uhlig, X-FAB Dresden GmbH &amp; Co. KG</i>	
<b>SESSION 6 (WB-P) – Wide Bandgap Posters</b>	
<b>WB-P-1 High-Voltage AlGaN/GaN Schottky Barrier Diodes on Si Substrate with Low-Temperature GaN Cap Layer for Edge Termination .....</b>	<b>225</b>
<i>A. Kamada, K. Matsubayashi, and A. Nakagawa, New Japan Radio Co., Ltd.; Y. Terada and T. Egawa, Nagoya Institute of Technology</i>	
<b>WB-P-2 High Frequency Switching of SiC High Voltage LJFET .....</b>	<b>229</b>
<i>Kuang Sheng, Yongxi Zhang, Ming Su, Liangchun Yu, and Jian H. Zhao, Rutgers University</i>	
<b>WB-P-3 Integration of 1200V SiC BJT with SiC Diode .....</b>	<b>233</b>
<i>Yan Gao and Alex Q. Huang, North Carolina State University; Anant K. Agarwal and Qingchun Zhang, Cree Inc.</i>	
<b>WB-P-4 The Effect of the Temperature on the Bipolar Degradation of 3.3 kV 4H-SiC PiN Diodes .....</b>	<b>237</b>
<i>P. Brosselard, A. Perez-Tómas, and N. Camara, CNM-CSIC; J. Hassan, Norstel AB; X. Jordà, M. Vellvehi, P. Godignon, and J. Millán, CNM-CSIC; J.P. Bergman, Norstel AB</i>	
<b>WB-P-5 High Breakdown Voltage AlGaN/GaN HEMTs by Employing Proton Implantation .....</b>	<b>241</b>
<i>Kyu-Heon Cho, In-Hwan Ji, Young-Hwan Choi, Jiyong Lim, and Young-Shil Kim, Seoul National University; Kye-Ryung Kim, Korea Atomic Energy Research Institute; Min-Koo Han, Seoul National University</i>	
<b>WB-P-6 Surge Current Ruggedness of Silicon Carbide Schottky- and Merged-PiN-Schottky Diodes .....</b>	<b>245</b>
<i>Birk Heinze and Josef Lutz, Chemnitz University of Technology; Matthias Neumeister, Siemens AG; Roland Rupp and Matthias Holz, Infineon Technologies AG</i>	

**WB-P-7 High Conductivity  $\delta$ -Doped Single Crystal Diamond Schottky m-i-p+ Diodes** ..... 249  
S.J. Rashid and F. Udrea, *University of Cambridge*; D.J. Twitchen and R.S. Balmer, *Element Six Ltd.*;  
G.A.J. Amaratunga, *University of Cambridge*

**WB-P-9 State of the Art 10 kV NMOS Transistors** ..... 253  
Mrinal K. Das, Robert Callanan, D. Craig Capell, Brett Hull, Fatima Husna, James Richmond, Michael O'loughlin,  
Michael J. Paisley, Adrian Powell, and Qingchun Zhang, *Cree, Inc.*

## Wednesday - May 21, 2008

**8:30 am – 10:35 am**

**SESSION 7 (WB1) – SiC Power Diodes, Switches and Packaging**

**Chairs:** Masakatsu Hoshi, *Nissan Motor Co. Ltd.*  
Jose Millan, *Centro Nacional de Microelectrónica*

**8:30 am – 8:55 am**

**WB1-1 Heavily Electron-Irradiated High Resistive 4H-SiC Pin Diode for Turn-On Snubber of 200kVA Class High Power SiCGT Inverter** ..... 256  
Katsunori Asano, Yoshitaka Sugawara, Atsushi Tanaka, Yoichi Miyanagi, Koji Nakayama, Shuji Ogata,  
Shinichi Okada, Toru Izumi, and Ryosuke Ishii, *Kansai Electric Power Company, Inc.*

**8:55 am – 9:20 am**

**WB1-2 Normally-Off SiC VJFETs for 800V and 1200V Power Switching Applications** ..... 260  
I. Sankin, D.C. Sheridan, W. Draper, V. Bondarenko, R. Kelley, M.S. Mazzola, and J.B. Casady, *SemiSouth Laboratories, Inc.*

**9:20 am – 9:45 am**

**WB1-3 4H-SiC Double RESURF MOSFETs with a Record Performance by Increasing RESURF Dose** ..... 263  
Masato Noborio, Jun Suda, and Tsunenobu Kimoto, *Kyoto University*

**9:45 am – 10:10 am**

**WB1-4 4.5 kV 1000 A Class SiC pn Diode Modules with Resin Mold Package and Ceramic Flat Package** ..... 267  
Y. Sugawara, S. Ogata, S. Okada, T. Izumi, Y. Miyanagi, K. Asano, K. Nakayama, and A. Tanaka, *Kansai Electric Power Co.*

**10:55 am – 12:35 pm**

**SESSION 8 (LV2) – Integrated LDMOS**

**Chairs:** Vishnu Khemka, *Freescale Semiconductor*  
Akio Nakagawa, *Toshiba*

**10:55 am – 11:20 am**

**LV2-1 Innovative Lateral Field Plates by Gate Fingers on STI Regions in Deep Submicron CMOS** ..... 271  
A. Heringa, J. Šonský, and J. Perez-Gonzalez, *NXP-TSMC Research Center*; R.Y. Su, *National Tsing Hua University*;  
P.Y. Chiang, *TSMC*



11:20 am – 11:45 am

- LV2-2 High Voltage P-Channel MOS Breakdown Voltage Instability During High Temperature Gate Stress Induced by Pre-Metal Nitride Layers** ..... 275  
G. Marchesi, J. Cambieri, A. Dundulachi, G. Pizzo, F. Pozzobon, M. Annese, A. Andreini, and G. Croce, *STMicroelectronics*

11:45 am – 12:10 pm

- LV2-3 Incremental FRESURF LDMOSFET Structure for Enhanced Voltage Blocking Capability on a 0.13 $\mu$ m, SOI Based Technology** ..... 279  
Tahir Khan, Vishnu Khemka, and Ronghua Zhu, *Freescale Semiconductor*

12:10 pm – 12:35 pm

- LV2-4 High Doped Drain Double-Resurf 100V P-Channel MOS on SOI 0.35  $\mu$ m BCD Technology** ..... 283  
Vincenzo Palumbo, Mirko Venturato, Michele Gallo, Fiorella Pozzobon, Maria Paola Galbiati, and Claudio Contiero, *STMicroelectronics*

2:00 pm – 3:15 pm

**SESSION 9 (WB2) – GaN Power HEMT/MOS Devices**  
Chairs: Hsueh-Rong Chang, *International Rectifier*

2:00 pm – 2:25 pm

- WB2-1 High Power AlGaN/GaN HFET with a High Breakdown Voltage of Over 1.8 kV on 4 Inch Si Substrates and the Suppression of Current Collapse** ..... 287  
Nariaki Ikeda, Syuusuke Kaya, Jiang Li, Yoshihiro Sato, Sadahiro Kato, and Seikoh Yoshida, *Furukawa Electric Co., Ltd.*

2:25 pm – 2:50 pm

- WB2-2 Lateral Implanted RESURF GaN MOSFETs with BV Up to 2.5kV** ..... 291  
W. Huang, T.P. Chow, *Rensselaer Polytechnic Institute*; Y. Niiyama, T. Nomura, and S. Yoshida, *Furukawa Electric Co., Ltd.*

2:50 pm – 3:15 pm

- WB2-3 Enhancement-Mode GaN Hybrid MOS-HEMTs with  $R_{on,sp}$  of 20 m $\Omega$ -cm<sup>2</sup>** ..... 295  
W. Huang and Z. Li, *Rensselaer Polytechnic Institute*; T.P. Chow, *Furukawa Electric Co., Ltd.*; Y. Niiyama, T. Nomura, and S. Yoshida, *Rensselaer Polytechnic Institute*

## Thursday - May 22, 2008

8:30 am – 10:10 am

**SESSION 10 (HV3) – Superjunction and Termination Technology**  
Chairs: Deva Pattanayak, *Vishay*  
J.-L. Sanchez, *LAAS CNR*

8:30 am – 8:55 am

- HV3-1 600V-Class Super Junction MOSFET with High Aspect Ratio P/N Columns Structure** ..... 299  
Jun Sakakibara, Yoshitaka Noda, and Takumi Shibata, *DENSO Corporation*; Shoji Nogami and Tomonori Yamaoka, *SUMCO Corporation*; Hitoshi Yamaguchi, *DENSO Corporation*

8:55 am – 9:20 am

- HV3-2 Feasibility Study of a Junction Termination Using Deep Trench Isolation Technique for the Realization of DT-SJMOSFETs** ..... 303  
H. Mahfoz-Kotb, *LAAS-CNRS*; L. Théolier, *LAAS-CNRS, Université de Toulouse*; F. Morancho, *LAAS-CNRS*; K. Isoird, *LAAS-CNRS, Université de Toulouse*; P. Dubreuil and T. Do Conto, *LAAS-CNRS*

9:20 am – 9:45 am

**HV3-3 Time-Periodic Avalanche Breakdown at the Edge Termination of Power Devices** ..... 307  
U. Knipper and G. Wachutka, *Munich University of Technology*; F. Pfirsch, T. Raker, and J. Niedermeyer, *Infineon Technologies AG*

9:45 am – 10:10 am

**HV3-4 The 2nd Generation Divided RESURF Structure for High Voltage ICs** ..... 311  
Kazuhiro Shimizu and Tomohide Terashima, *Mitsubishi Electric Corporation*

10:30 am – 12:10 pm

**SESSION 11 (IP2) – Power IC Applications**

**Chairs:** Sujit Banerjee, *Power Integrations*  
Wai Tung Ng, *University of Toronto*

10:30 am – 10:55 am

**IP2-1 System in Package with Mounted Capacitor for Reduced Parasitic Inductance in Voltage Regulators** ..... 315  
T. Hashimoto and T. Kawashima, *Hitachi Ltd.*; T. Uno, Y. Satou, and N. Matsuura, *Renesas Technology Corp.*

10:55 am – 11:20 am

**IP2-2 1700V Fully Coreless Gate Driver with Rugged Signal Interface and Switching-Independent Power Supply** ..... 319  
Sascha Pawel and Jan Thalheim, *CT-Concept Technology Ltd.*

11:20 am – 11:45 am

**IP2-3 Three-Input Type Single-Chip Inverter IC Including a Function to Generate Six Signals and Dead Time** ..... 323  
Kenji Sakurai, Daisuke Maeda, and Hiroyuki Hasegawa, *Hitachi Ltd.*

11:45 am – 12:10 pm

**IP2-4 Thick Silicon Membrane Technology for Reliable and High Performance Operation of High Voltage LIGBTs in Power ICs** ..... 327  
T. Trajkovic, F. Udrea, C. Lee, N. Udugampola, V. Pathirana, A. Mihaila, and G.A.J. Amaratunga, *Cambridge Semiconductor Ltd.*